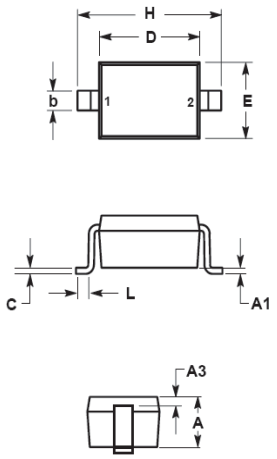
BZT52B2V4S~BZT52B75S

SURFACE MOUNT ZENMER DIODE

Features

- Wide zener voltage range selection : 2.4V to 75V.
- VZ Tolerance Selection of ±2%.
- General Purpose, Medium Current.
- Ideally Suited for Automated Assembly Processes.
- Available in Lead Free Version.



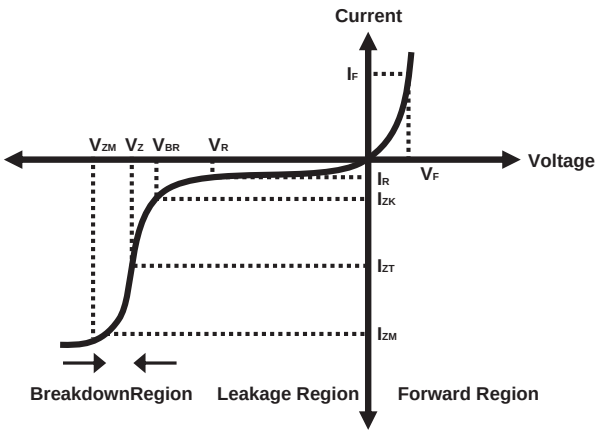
SOD-323		
Dim.	Min.	Max.
A	0.80	1.10
A1	0.00	0.10
A3	0.15 REF	
B	0.25	0.40
C	0.10	0.15
D	1.60	1.80
E	1.15	1.35
L	0.20	0.50
H	2.30	2.80
Dimensions in millimeter		

Maximum Ratings @ T_A = 25°C unless otherwise specified

Parameter	Symbol	Value	Unit
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{Stg}	- 55 to + 150	°C
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	625	°C/W
Forward Voltage at I_F = 10 mA	V_F	0.9	V

1) Device mounted on ceramic PCB: 7.6mm x 9.4mm x 0.87mm with pad areas 25mm²
2) Short duration test pulse used to minimize self-heating effect
3) f=1KHz

Zener I vs. V Characteristics



V_{BR} : Voltage at I_{ZK}
I_{ZK} : Test current for voltage V_{BR}
Z_{ZK} : Dynamic impedance at I_{ZK}
I_{ZT} : Test current for voltage V_Z
V_Z : Voltage at current I_{ZT}
Z_{ZT} : Dynamic impedance at I_{ZT}
I_{ZM} : Maximum steady state current
V_{ZM} : Voltage at I_{ZM}

HAICHUANG SEMI

BZT52B2V4S~BZT52B75S

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Electrical Characteristics @ T_A = 25°C unless otherwise specified

Device	Marking	Zener Voltage Range				Maximum Zener Impedance 3)			Maximum Reverse Current		Typical Temperature coefficent @ IZTC=mV/℃		Test Current IZTC
		Vz@Izt			Izt	Zzt @Izt	Zzk @Izk	Izk	IR	VR			
		Nom(V)	Min(V)	Max(V)	mA	Ω		mA	uA	V	Min	Max	mA
BZT52B2V4S	2WX	2.4	2.35	2.45	5	100	600	1.0	50	1.0	-3.5	0	5
BZT52B2V7S	2W1	2.7	2.65	2.75	5	100	600	1.0	20	1.0	-3.5	0	5
BZT52B3V0S	2W2	3.0	2.94	3.06	5	95	600	1.0	10	1.0	-3.5	0	5
BZT52B3V3S	2W3	3.3	3.23	3.37	5	95	600	1.0	5	1.0	-3.5	0	5
BZT52B3V6S	2W4	3.6	3.53	3.67	5	90	600	1.0	5	1.0	-3.5	0	5
BZT52B3V9S	2W5	3.9	3.82	3.98	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52B4V3S	2W6	4.3	4.21	4.39	5	90	600	1.0	3	1.0	-3.5	0	5
BZT52B4V7S	2W7	4.7	4.61	4.79	5	80	500	1.0	3	2.0	-3.5	0.2	5
BZT52B5V1S	2W8	5.1	5.00	5.20	5	60	480	1.0	2	2.0	-2.7	1.2	5
BZT52B5V6S	2W9	5.6	5.49	5.71	5	40	400	1.0	1	2.0	-2.0	2.5	5
BZT52B6V2S	2WA	6.2	6.08	6.32	5	10	150	1.0	3	4.0	0.4	3.7	5
BZT52B6V8S	2WB	6.8	6.66	6.94	5	15	80	1.0	2	4.0	1.2	4.5	5
BZT52B7V5S	2WC	7.5	7.35	7.65	5	15	80	1.0	1	5.0	2.5	5.3	5
BZT52B8V2S	2WD	8.2	8.04	8.36	5	15	80	1.0	0.7	5.0	3.2	6.2	5
BZT52B9V1S	2WE	9.1	8.92	9.28	5	15	100	1.0	0.5	6.0	3.8	7.0	5
BZT52B10S	2WF	10	9.80	10.20	5	20	150	1.0	0.2	7.0	4.5	8.0	5
BZT52B11S	2WG	11	10.78	11.22	5	20	150	1.0	0.1	8.0	5.4	9.0	5
BZT52B12S	2WH	12	11.76	12.24	5	25	150	1.0	0.1	8.0	6.0	10.0	5
BZT52B13S	2WI	13	12.74	13.26	5	30	170	1.0	0.1	8.0	7.0	11.0	5
BZT52B15S	2WJ	15	14.70	15.30	5	30	200	1.0	0.1	10.5	9.2	13.0	5
BZT52B16S	2WK	16	15.68	16.32	5	40	200	1.0	0.1	11.2	10.4	14.0	5
BZT52B18S	2WL	18	17.64	18.36	5	45	225	1.0	0.1	12.6	12.4	16.0	5
BZT52B20S	2WM	20	19.60	20.40	5	55	225	1.0	0.1	14.0	14.4	18.0	5
BZT52B22S	2WN	22	21.56	22.44	5	55	250	1.0	0.1	15.4	16.4	20.0	5
BZT52B24S	2WO	24	23.52	24.48	5	70	250	1.0	0.1	16.8	18.4	22.0	5
BZT52B27S	2WP	27	26.46	27.54	2	80	300	0.5	0.1	18.9	21.4	25.3	2
BZT52B30S	2WQ	30	29.40	30.60	2	80	300	0.5	0.1	21.0	24.4	29.4	2
BZT52B33S	2WR	33	32.34	33.66	2	80	325	0.5	0.1	23.1	27.4	33.4	2
BZT52B36S	2WS	36	35.28	36.72	2	90	350	0.5	0.1	25.2	30.4	37.4	2
BZT52B39S	2WT	39	38.22	39.78	2	130	350	0.5	0.1	27.3	33.4	41.2	2
BZT52B43S	2WU	43	42.14	43.86	2	100	700	1.0	0.1	32.0	10.0	12.0	5
BZT52B47S	2WV	47	46.06	47.94	2	100	750	1.0	0.1	35.0	10.0	12.0	5
BZT52B51S	2WW	51	49.98	52.02	2	125	750	1.0	0.1	38.0	10.0	12.0	5
BZT52B56S	2XW	56	54.88	57.12	2	135	700	1.0	0.1	39.0	10.0	12.0	5
BZT52B62S	6E2	62	60.76	63.24	2	200	1000	1.0	0.2	47.0	10.0	12.0	5
BZT52B68S	6F2	68	66.64	69.36	2	250	1000	1.0	0.2	52.0	10.0	12.0	5
BZT52B75S	6H2	75	73.50	76.50	2	300	1000	1.0	0.2	57	10.0	12.0	5

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TYPICAL TRANSIENT CHARACTERISTICS

FIG 1 Typical Forward Characteristics

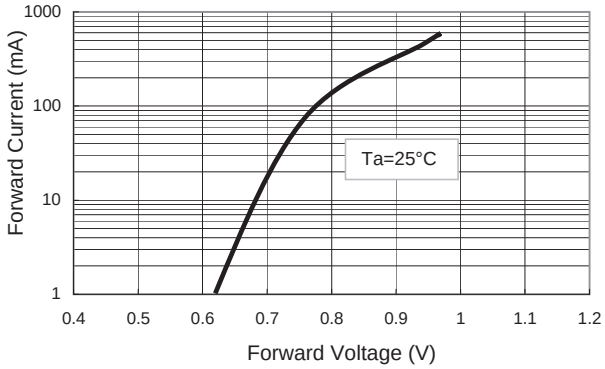


FIG 2 Zener Breakdown Characteristics

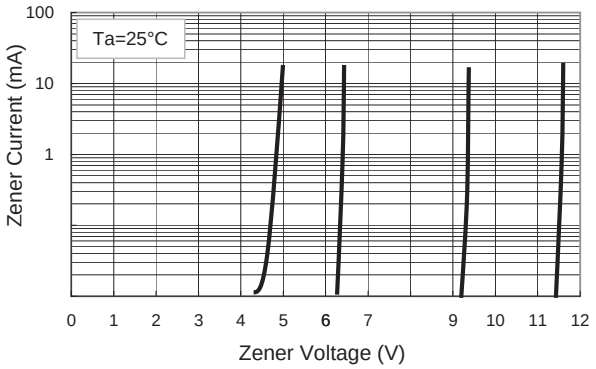


FIG 3 Zener Breakdown Characteristics

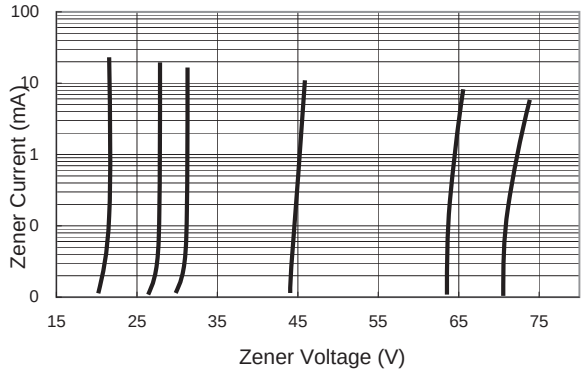


FIG 4 Admissible Power Disspation Curve

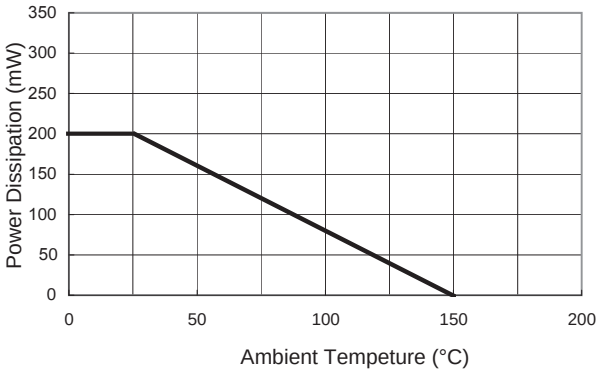


FIG 5 Typical Capacitance

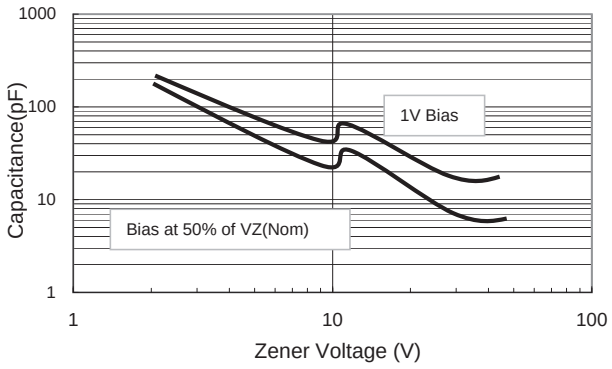
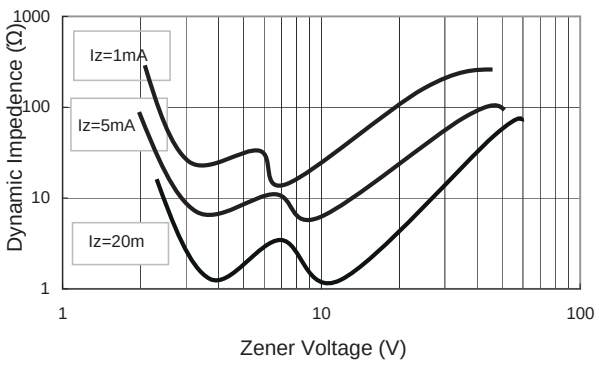


FIG 6 Effect of Zener Voltage on Impedence



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